MGBR10L30 Preliminary DIODE

# MOS GATED BARRIER RECTIFIER

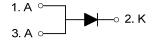
#### **■** DESCRIPTION

The UTC MGBR10L30 is a surface mount mos gatedbarrier rectifier, it uses UTC's advanced technology to provide customers withlow forward voltage drop and high switching speed, etc.

#### ■ FEATURES

- \* Low forward voltage drop
- \* High switching speed

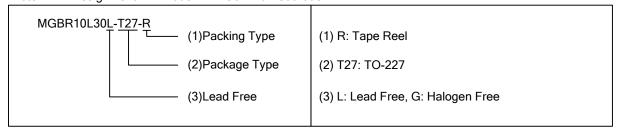
#### ■ SYMBOL



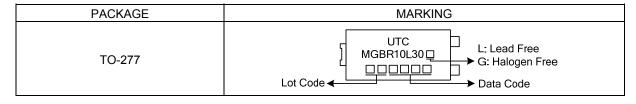
# **■ ORDERING INFORMATION**

Ordering Number		Daalaaaa	Pin Assignment			Daaliaa	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MGBR10L30L-T27-R	MGBR10L30G-T27-R	TO-277	Α	K	Α	Tape Reel	

Note: Pin Assignment: A: Anode K: Common Cathode



## ■ MARKING INFORMATION



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TO-277

# ■ **ABSOLUTE MAXIMUM RATINGS**(T<sub>A</sub>=25°C, unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER	SYMBOL	RATINGS	UNIT
DC Blocking Voltage	$V_{RM}$	30	V
WorkingPeak Reverse Voltage	$V_{RWM}$	30	V
Peak Repetitive Reverse Voltage	$V_{RRM}$	30	V
RMS Reverse Voltage	$V_{R(RMS)}$	21	V
Average Rectified Output Current T <sub>C</sub> =140°C	10	10	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load	I <sub>FSM</sub>	200	Α
Repetitive Peak Avalanche Power (1µs, 25°C)	P <sub>ARM</sub>	5000	W
Operating Junction Temperature	TJ	-65~+150	°C
Storage Temperature	T <sub>STG</sub>	-65~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

# ■ THERMAL CHARACTERISTICS (Note 3)

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	73	°C/W
Junction to Case	θ <sub>JC</sub>	13	°C/W

## ■ **ELECTRICAL CHARACTERISTICS**(T<sub>A</sub>=25°C,unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I <sub>R</sub> =1mA	30			V
Farmed Valtage Days	VEM	I <sub>F</sub> =10A, T <sub>J</sub> =25°C			0.55	V
Forward Voltage Drop		I <sub>F</sub> =10A, T <sub>J</sub> =125°C			0.52	V
Leakage Current (Note 1)	l low	V <sub>R</sub> =30V, T <sub>J</sub> =25°C		100	500	μΑ
		V <sub>R</sub> =30V, T <sub>J</sub> =125°C		12	40	mA

Notes: 1. Short duration pulse test used to minimize self-heating effect.

- 2. Thermal resistance junction to case mounted on heatsink.
- 3. Mounted on an FR4 PCB, single-sided copper, with 100 cm<sup>2</sup> copper pad area.

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